MSKSEMI















ESD

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Broduct data sheet











TRANSISTOR (NPN)

FEATURES

- High DC current gain :h_{FE}=200(Typ) V_{CE}=6V,I_C=1mA
- High voltage:V_{CEO}=50V

1. BASE

- 2. EMITTER
- 3. COLLECTOR

CLASSIFICATION OF hFE

Rank	L4	L5	L6	L7
Range	90-180	135-270	200-400	300-600
Marking	L4	L5	L6	L7

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{СВО}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5	٧
Ic	Collector Current	100	mA
Pc	Collector Power Dissipation	200	mW
$R_{\Theta JA}$	Thermal Resistance From Junction To Ambient	625	°CW
T_J, T_stg	Operation Junction and Storage Temperature Range	-55~+150	°C

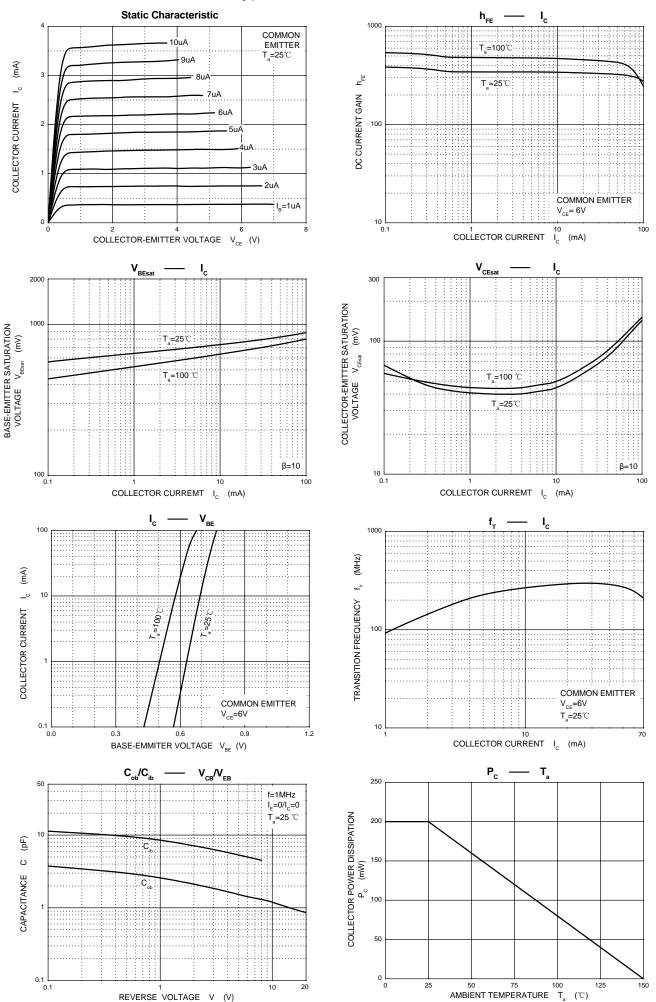
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA,I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA,I _B =0	50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA,I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =60V,I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V,I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =6V,I _C =1mA	90	200	600	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100mA,I _B =10mA			0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =100mA,I _B =10mA			1	V
Transition frequency	f⊤	V _{CE} =6V,I _C =10mA		250		MHz

Semiconductor

Compiance

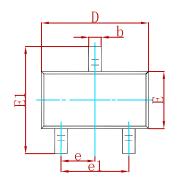
Typical Characteristics

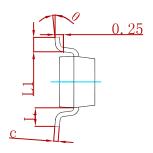


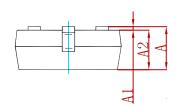




PACKAGE MECHANICAL DATA

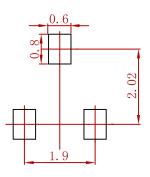






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
2SC1623-MS	SOT-23	3000



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